74HC4066; 74HCT4066

Quad single-pole single-throw analog switch Rev. 8 — 3 December 2015

Product data sheet

1. **General description**

The 74HC4066; 74HCT4066 is a quad single pole, single throw analog switch. Each switch features two input/output terminals (nY and nZ) and an active HIGH enable input (nE). When nE is LOW, the analog switch is turned off. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

Features and benefits 2.

- Input levels nE inputs:
 - ◆ For 74HC4066: CMOS level
 - ◆ For 74HCT4066: TTL level
- Low ON resistance:
 - 50 Ω (typical) at $V_{CC} = 4.5 \text{ V}$
 - ◆ 45 Ω (typical) at V_{CC} = 6.0 V
 - 35 Ω (typical) at $V_{CC} = 9.0 \text{ V}$
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

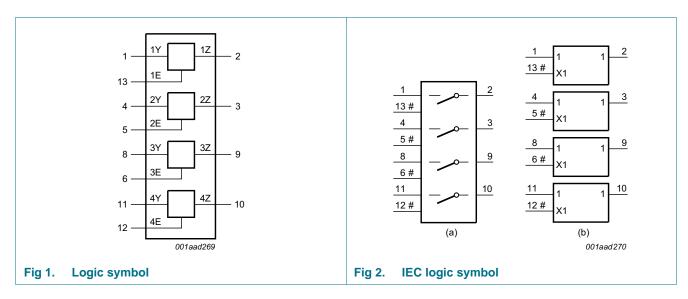


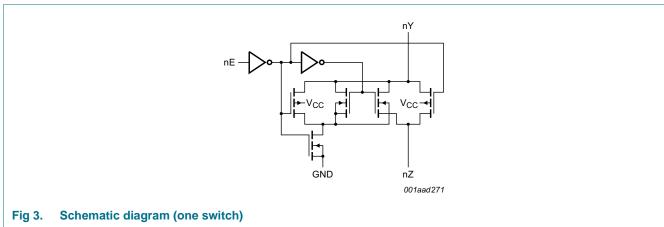
3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74HC4066D	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1				
74HCT4066D			3.9 mm					
74HC4066DB	−40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1				
74HCT4066DB			width 5.3 mm					
74HC4066PW	-40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body	SOT402-1				
74HCT4066PW			width 4.4 mm					
74HC4066BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1				
74HCT4066BQ			thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm					

4. Functional diagram





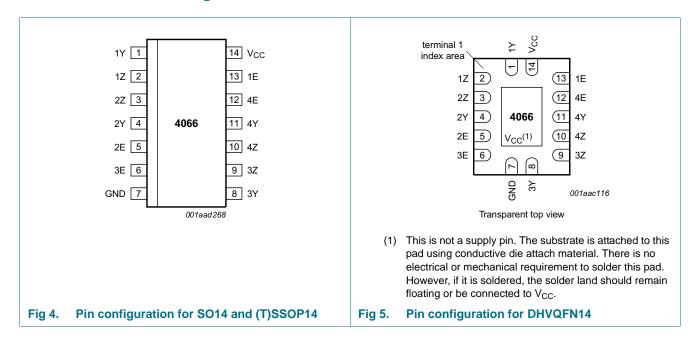
74HC_HCT4066

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5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

•		
Symbol	Pin	Description
1Z, 2Z, 3Z, 4Z	2, 3, 9, 10	independent input or output
1Y, 2Y, 3Y, 4Y	1, 4, 8, 11	independent input or output
GND	7	ground (0 V)
1E, 2E, 3E, 4E	13, 5, 6, 12	enable input (active HIGH)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Input nE	Switch
L	OFF
Н	ON

[1] H = HIGH voltage level;L = LOW voltage level.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+11.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I _{SK}	switch clamping current	V_{SW} < -0.5 V or V_{SW} > V_{CC} + 0.5 V		-	±20	mA
I _{SW}	switch current	$V_{SW} = -0.5 \text{ V to } V_{CC} + 0.5 \text{ V}$	<u>[1]</u>	-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-	-50	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2]			
		SO14, (T)SSOP14 and DHVQFN14 packages		-	500	mW
Р	power dissipation	per switch		-	100	mW

^[1] To avoid drawing V_{CC} current out of terminal Z, when switch current flows in terminals Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no V_{CC} current will flow out of terminals Yn. In this case there is no limit for the voltage drop across the switch, but the voltages at Yn and Z may not exceed V_{CC} or GND.

For (T)SSOP14 packages: Ptot derates linearly with 5.5 mW/K above 60 °C.

For DHVQFN14 packages: P_{tot} derates linearly with 4.5 mW/K above 60 $^{\circ}\text{C}.$

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions 74HC4066 74HCT4066				66	Unit		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	10.0	4.5	5.0	5.5	V
VI	input voltage		GND	-	V _{CC}	GND	-	V _{CC}	V
V_{SW}	switch voltage		GND	-	V _{CC}	GND	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
	and fall rate	V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V
		V _{CC} = 10.0 V	-	-	35	-	-	-	ns/V

^[2] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Static characteristics

Table 6. R_{ON} resistance per switch for types 74HC4066 and 74HCT4066

 $V_I = V_{IH}$ or V_{IL} ; for test circuit see <u>Figure 6</u>.

 V_{is} is the input voltage at a Yn or \overline{Z} terminal, whichever is assigned as an input.

 V_{os} is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

For 74HC4066: V_{CC} – GND = 2.0 V, 4.5 V, 6.0 V and 9.0 V.

For 74HCT4066: V_{CC} – GND = 4.5 V.

Symbol	Parameter	Conditions	-40 °C to +85 °C			–40 °C to	Unit	
			Min	Typ[1]	Max	Min	Max	
R _{ON(peak)}	ON resistance (peak)	V _{is} = V _{CC} to GND						
		$V_{CC} = 2.0 \text{ V}; I_{SW} = 100 \mu\text{A}$	-	-	-	-	-	Ω
		$V_{CC} = 4.5 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	54	-	118	142	Ω
		$V_{CC} = 6.0 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	42	-	105	126	Ω
		$V_{CC} = 9.0 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	32	-	88	105	Ω
R _{ON(rail)}	ON resistance (rail)	V _{is} = GND						
		$V_{CC} = 2.0 \text{ V}; I_{SW} = 100 \mu\text{A}$	-	80	-	-	-	Ω
		$V_{CC} = 4.5 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	35	-	95	115	Ω
		$V_{CC} = 6.0 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	27	-	82	100	Ω
		$V_{CC} = 9.0 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	20	-	70	85	Ω
		$V_{is} = V_{CC}$						
		$V_{CC} = 2.0 \text{ V}; I_{SW} = 100 \mu\text{A}$	-	100	-	-	-	Ω
		$V_{CC} = 4.5 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	42	-	106	128	Ω
		$V_{CC} = 6.0 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	35	-	94	113	Ω
		$V_{CC} = 9.0 \text{ V}; I_{SW} = 1000 \mu\text{A}$	-	20	-	78	95	Ω
ΔR _{ON}	ON resistance	V _{is} = V _{CC} to GND						
	mismatch between channels	$V_{CC} = 2.0 \text{ V}$ [2]	-	-	-	-	-	Ω
	Chameis	V _{CC} = 4.5 V	-	5	-	-	-	Ω
		V _{CC} = 6.0 V	-	4	-	-	-	Ω
		V _{CC} = 9.0 V	-	3	-	-	-	Ω

^[1] Typical values are measured at T_{amb} = 25 °C.

^[2] At supply voltages (V_{CC} – GND) approaching 2 V, the analog switch ON resistance becomes extremely non-linear. Therefore it is recommended that these devices be used to transmit digital signals only, when using these supply voltages.

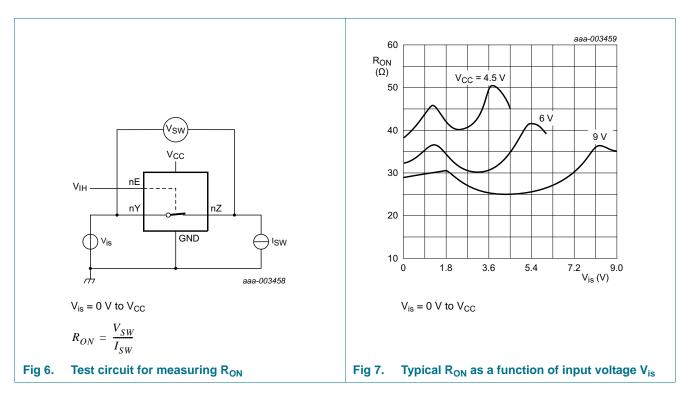


Table 7. Static characteristics 74HC4066

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input.

Vos is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T _{amb} = -40	°C to +85 °C	'				
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	V
		V _{CC} = 9.0 V	6.3	4.7	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.80	V
		V _{CC} = 9.0 V	-	4.3	2.70	V
l _l	input leakage current	V _I = V _{CC} or GND				
		V _{CC} = 6.0 V	-	-	±1.0	μΑ
		V _{CC} = 10.0 V	-	-	±2.0	μΑ
I _{S(OFF)}	OFF-state leakage current	$V_{CC} = 10.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 8}}{\text{Figure 8}}$				
		per channel	-	-	±1.0	μΑ
I _{S(ON)}	ON-state leakage current	$V_{CC} = 10.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 9}}{\text{Figure 1}}$	-	-	±1.0	μА

 Table 7.
 Static characteristics 74HC4066 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

 V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input.

Vos is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{is} = GND$ or V_{CC} ; $V_{os} = V_{CC}$ or GND				
		V _{CC} = 6.0 V	-	-	20.0	μΑ
		V _{CC} = 10.0 V	-	-	40.0	μΑ
Cı	input capacitance		-	3.5	-	pF
C _{sw}	switch capacitance		-	8	-	pF
T _{amb} = -4	0 °C to +125 °C				l	_
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		$V_{CC} = 4.5 \text{ V}$	3.15	-	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	-	-	V
V _{IL}		$V_{CC} = 9.0 \text{ V}$	6.3	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.50	V
		$V_{CC} = 4.5 \text{ V}$	-	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	-	1.80	V
		$V_{CC} = 9.0 \text{ V}$	-	- 40.0 3.5 - 8 0.50 - 1.35	V	
l _l	input leakage current	$V_I = V_{CC}$ or GND				
		V _{CC} = 6.0 V	-	-	±1.0	μΑ
		V _{CC} = 10.0 V	-	-	±2.0	μΑ
I _{S(OFF)}	OFF-state leakage current	$V_{CC} = 10.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 8}}{\text{Figure 8}}$				
		per channel	-	-	±1.0	μА
I _{S(ON)}	ON-state leakage current	$V_{CC} = 10.0 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 9}}{\text{Figure 9}}$	-	-	±1.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{is} = GND$ or V_{CC} ; $V_{os} = V_{CC}$ or GND				
		V _{CC} = 6.0 V	-	-	40	μΑ
		V _{CC} = 10.0 V	-	-	80	μΑ

^[1] Typical values are measured at T_{amb} = 25 °C.

Table 8. Static characteristics 74HCT4066

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

 V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input.

 V_{os} is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

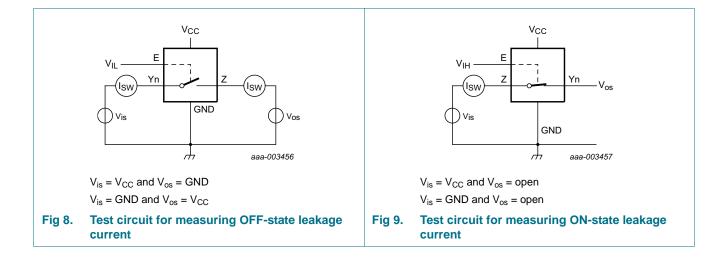
Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit		
$T_{amb} = -40$	T _{amb} = -40 °C to +85 °C							
V_{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V		
V_{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V		
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ		

Table 8. Static characteristics 74HCT4066 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V). V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input. V_{os} is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
I _{S(OFF)}	OFF-state leakage current	$V_{CC} = 5.5 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 8}}{\text{Figure 8}}$				
		per channel	-	-	±1.0	μΑ
I _{S(ON)}	ON-state leakage current	$V_{CC} = 5.5 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 9}}{\text{Figure 9}}$	-	-	±1.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{is} = GND$ or V_{CC} ; $V_{os} = V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V	-	-	20.0	μА
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	100	450	μА
Cı	input capacitance		-	3.5	-	pF
C _{sw}	switch capacitance		-	8	-	pF
T _{amb} = -40	°C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
I _{S(OFF)}	OFF-state leakage current	$V_{CC} = 5.5 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 8}}{\text{Figure 8}}$				
		per channel	-	-	±1.0	μΑ
I _{S(ON)}	ON-state leakage current	$V_{CC} = 5.5 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - \text{GND}; \text{ see } \frac{\text{Figure 9}}{\text{Figure 9}}$	-	-	±1.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{is} = GND$ or V_{CC} ; $V_{os} = V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V	-	-	40	μА
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	490	μА

[1] Typical values are measured at T_{amb} = 25 °C.



10. Dynamic characteristics

Table 9. Dynamic characteristics 74HC4066

GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF unless specified otherwise; for test circuit see <u>Figure 12</u>.

 V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input.

Vos is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions		-40	°C to +85	o°C	–40 °C to	+125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	nY to nZ or nZ to nY; $R_L = \infty \Omega$; see <u>Figure 10</u>	[2]						
		V _{CC} = 2.0 V		-	8	75	-	90	ns
		V _{CC} = 4.5 V		-	3	15	-	18	ns
		V _{CC} = 6.0 V		-	2	13	-	15	ns
		V _{CC} = 9.0 V		-	2	10	-	12	ns
t_{off} turn-off time nE to nY or nZ; see Figure 11 $V_{CC} = 2.0 \text{ V}$ -									
		V _{CC} = 2.0 V		-	44	190	-	225	ns
		V _{CC} = 4.5 V		-	16	38	-	45	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	13	-	-	-	ns
		V _{CC} = 6.0 V		-	13	33	-	38	ns
		V _{CC} = 9.0 V		-	16	26	-	30	ns
t _{on}	turn-on time	nE to nY or nZ; see Figure 11	[3]					18 15 12 225 45 - 38 30 150 30 - 26 20	
		V _{CC} = 2.0 V		-	36	125	-	150	ns
		V _{CC} = 4.5 V		-	13	25	-	30	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns
		V _{CC} = 6.0 V		-	10	21	-	26	ns
		V _{CC} = 9.0 V		-	8	16	-	20	ns
C _{PD}	power dissipation capacitance	per switch; $V_I = GND$ to V_{CC}	<u>[5]</u>	11		-	-	-	pF

- [1] Typical values are measured at T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [3] t_{on} is the same as t_{PHZ} and t_{PLZ} .
- [4] t_{off} is the same as t_{PZH} and t_{PZL} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum \{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ where:

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 $\sum \{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\} = sum \text{ of outputs};$

C_L = output load capacitance in pF;

 C_{sw} = switch capacitance in pF;

 V_{CC} = supply voltage in V.

Table 10. Dynamic characteristics 74HCT4066

GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF unless specified otherwise; for test circuit see <u>Figure 12</u>.

 V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input.

Vos is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions		40 °C to +8	5 °C	–40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	nY to nZ or nZ to nY; $R_L = \infty \Omega$; see Figure 10						
		V _{CC} = 4.5 V	-	3	15	-	18	ns
t _{off}	turn-off time	nE to nY or nZ; see Figure 11						
		V _{CC} = 4.5 V	-	20	44	-	53	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	16	-	-	-	ns
t _{on}	turn-on time	nE to nY or nZ; see Figure 11						
		V _{CC} = 4.5 V	-	12	30	-	36	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	12	-	-	-	ns
C _{PD}	power dissipation capacitance	per switch; $V_I = GND$ to $(V_{CC} - 1.5 V)$	-	12	-	-	-	pF

- [1] Typical values are measured at T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PHL} and t_{PLH}.
- [3] t_{on} is the same as t_{PHZ} and t_{PLZ} .
- [4] t_{off} is the same as t_{PZH} and t_{PZL} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum \{(C_L + C_{sw}) \times V_{CC}{}^2 \times f_o\}$$
 where:

 f_i = input frequency in MHz;

fo = output frequency in MHz;

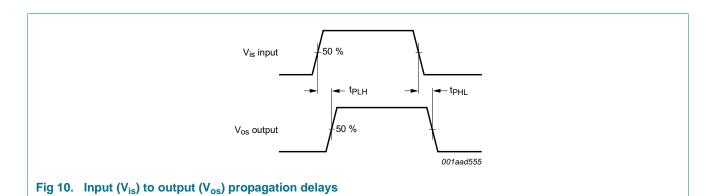
 $\Sigma \{ (C_L + C_{sw}) \times V_{CC}^2 \times f_0 \} = \text{sum of outputs};$

C_L = output load capacitance in pF;

C_{sw} = switch capacitance in pF;

 V_{CC} = supply voltage in V.

11. Waveforms



74HC_HCT4066

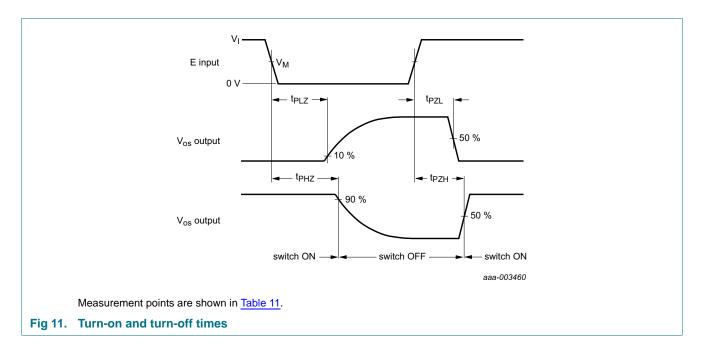
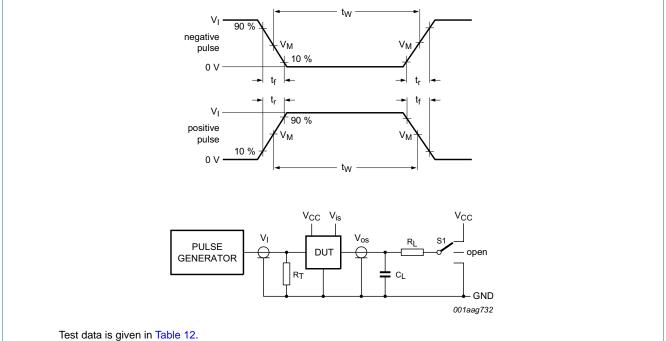


Table 11. Measurement points

Туре	V _I	V _M
74HC4066	V_{CC}	0.5V _{CC}
74HCT4066	3.0 V	1.3 V



rest data is given in table 12

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 12. Test circuit for measuring switching times

Table 12. Test data

Test	Input		Output	S1 position			
	Control E	Switch Yn (Z)	t _r , t _f	Switch Z (Yn)			
	V _I [1]	V _{is}		C _L	R _L		
t _{PHL} , t _{PLH}	GND	GND to V _{CC}	6 ns	50 pF	-	open	
t _{PHZ} , t _{PZH}	GND to V _{CC}	V _{CC}	6 ns	50 pF, 15 pF	1 kΩ	GND	
t _{PLZ} , t _{PZL}	GND to V _{CC}	GND	6 ns	50 pF, 15 pF	1 kΩ	V _{CC}	

[1] For 74HCT4066: maximum input voltage $V_1 = 3.0 \text{ V}$.

12. Additional dynamic characteristics

Table 13. Additional dynamic characteristics

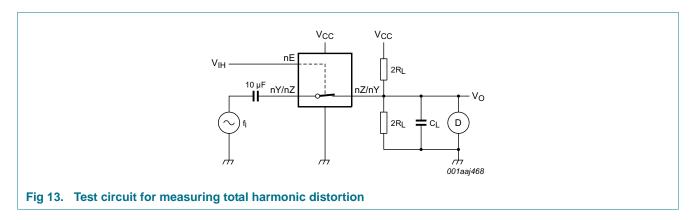
Recommended conditions and typical values; GND = 0 V; T_{amb} = 25 °C.

 V_{is} is the input voltage at a Yn or Z terminal, whichever is assigned as an input.

 V_{os} is the output voltage at a Yn or Z terminal, whichever is assigned as an output.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
THD	total harmonic distortion	f_i = 1 kHz; R_L = 10 k Ω ; C_L = 50 pF; see Figure 13				%
		V _{CC} = 4.5 V; V _I = 4.0 V (p-p)	-	0.04	-	%
		V _{CC} = 9.0 V; V _I = 8.0 V (p-p)	-	0.02	-	%
		f_i = 10 kHz; R_L = 10 k Ω ; C_L = 50 pF; see Figure 13				
		V _{CC} = 4.5 V; V _I = 4.0 V (p-p)	-	0.12	-	%
		$V_{CC} = 9.0 \text{ V}; V_I = 8.0 \text{ V (p-p)}$	-	0.06	-	%
f _(-3dB) -3 dB frequency response		$R_L = 50 \Omega$; $C_L = 10 pF$; see <u>Figure 15</u>				
		V _{CC} = 4.5 V	-	180	-	MHz
		V _{CC} = 9.0 V	-	200	-	MHz
α_{iso}	isolation (OFF-state)	$R_L = 600 \Omega$; $C_L = 50 pF$; $f_i = 1 MHz$; see Figure 14				
		V _{CC} = 4.5 V	-	-50	-	dB
		V _{CC} = 9.0 V	-	-50	-	dB
V _{ct}	crosstalk voltage	between digital input and switch (peak to peak value); $R_L = 600 \Omega$; $C_L = 50 pF$; $f_i = 1 MHz$; see Figure 16				
		V _{CC} = 4.5 V	-	110	-	mV
		V _{CC} = 9.0 V	-	220	-	mV
Xtalk	crosstalk	between switches; $R_L = 600 \Omega$; $C_L = 50 pF$; [1] $f_i = 1 \text{ MHz}$; see Figure 17				
		V _{CC} = 4.5 V	-	-60	-	dB
		V _{CC} = 9.0 V	-	-60	-	dB

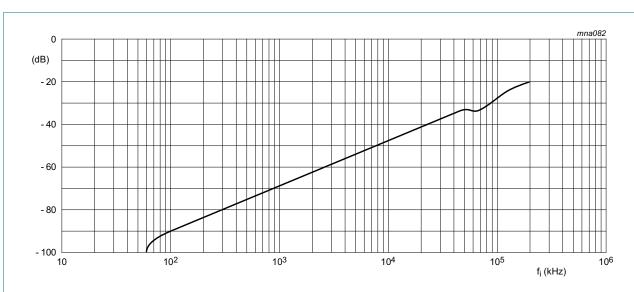
- [1] Adjust input voltage V_{is} to 0 dBm level (0 dBm = 1 mW into 600 Ω).
- [2] Adjust input voltage V_{is} to 0 dBm level at V_{os} for f_i = 1 MHz (0 dBm = 1 mW into 50 Ω). After set-up, f_i is increased to obtain a reading of -3 dB at V_{os} .



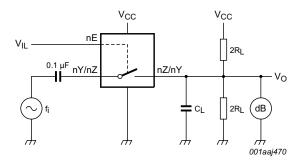
74HC_HCT4066

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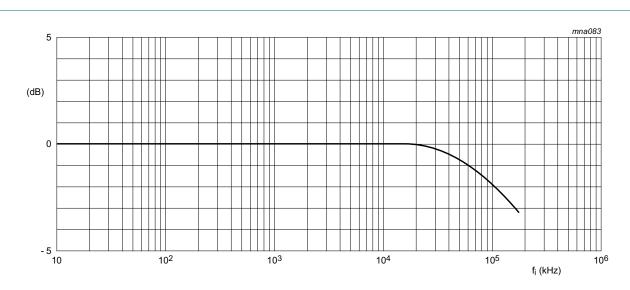
a. Isolation (OFF-state)



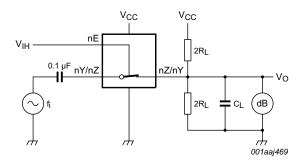
b. Test circuit

 V_{CC} = 4.5 V; GND = 0 V; R_L = 600 Ω ; R_{source} = 1 k Ω .

Fig 14. Isolation (OFF-state) as a function of frequency



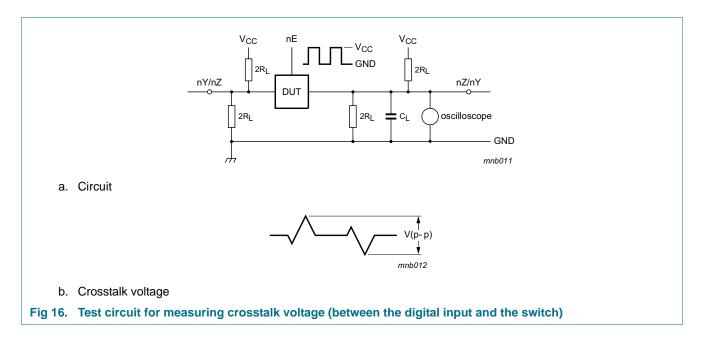
a. Typical -3 dB frequency response

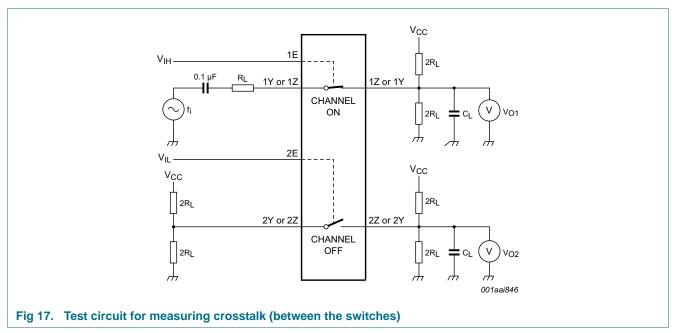


b. Test circuit

 V_{CC} = 4.5 V; GND = 0 V; R_L = 50 $\Omega;$ R_{source} = 1 $k\Omega.$

Fig 15. -3 dB frequency response

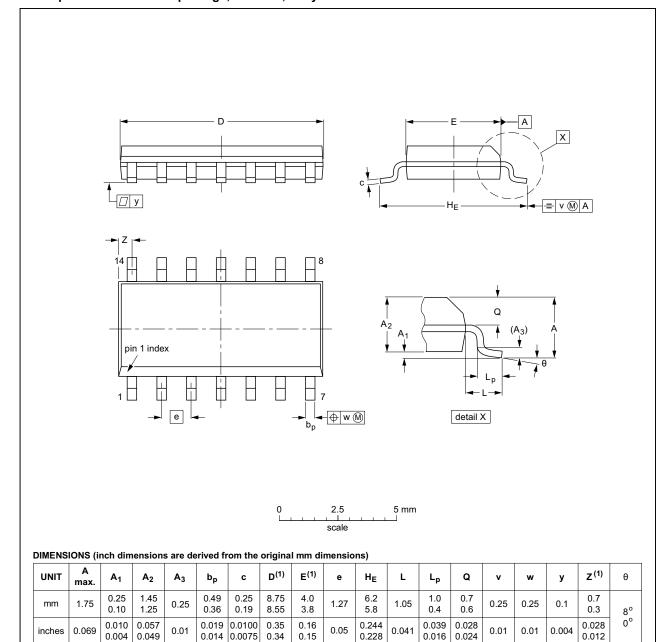




13. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT108-1	076E06	MS-012				99-12-27 03-02-19	

Fig 18. Package outline SOT108-1 (SO14)

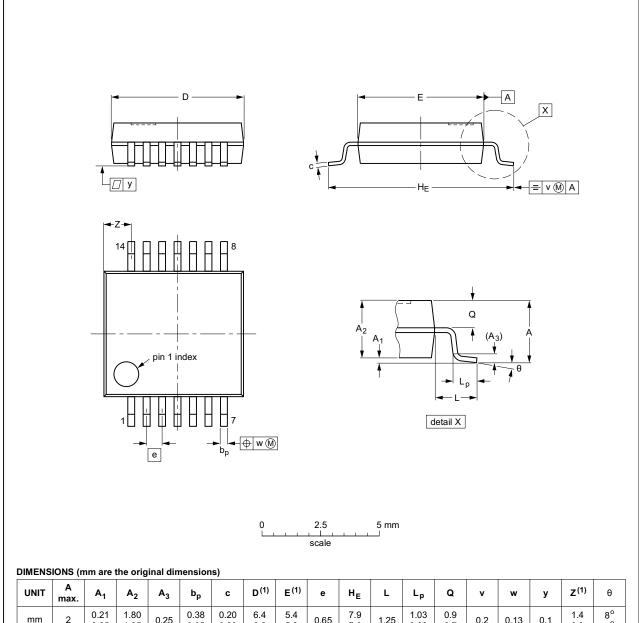
74HC_HCT4066

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



_	····-·································																		
	UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEDEC JEITA		PROJECTION	ISSUE DATE
SOT337-1		MO-150				99-12-27 03-02-19

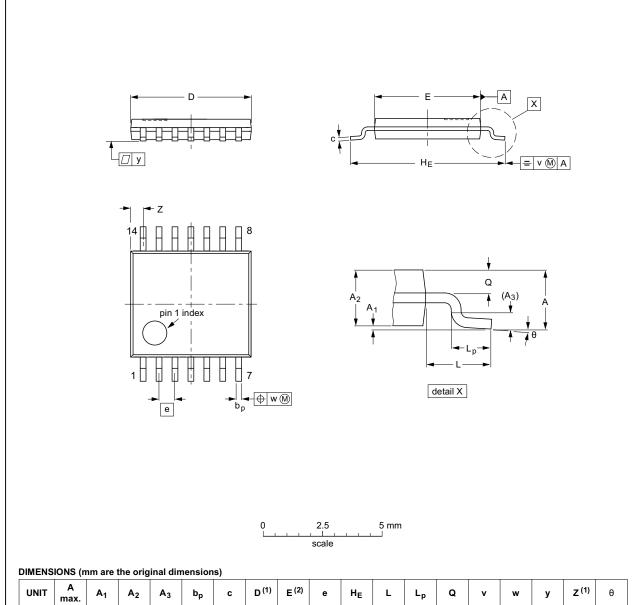
Fig 19. Package outline SOT337-1 (SSOP14)

74HC_HCT4066

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽²⁾	e	HE	L	Lp	Q	>	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT402-1		MO-153				99-12-27 03-02-18

Fig 20. Package outline SOT402-1 (TSSOP14)

74HC_HCT4066

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm

SOT762-1

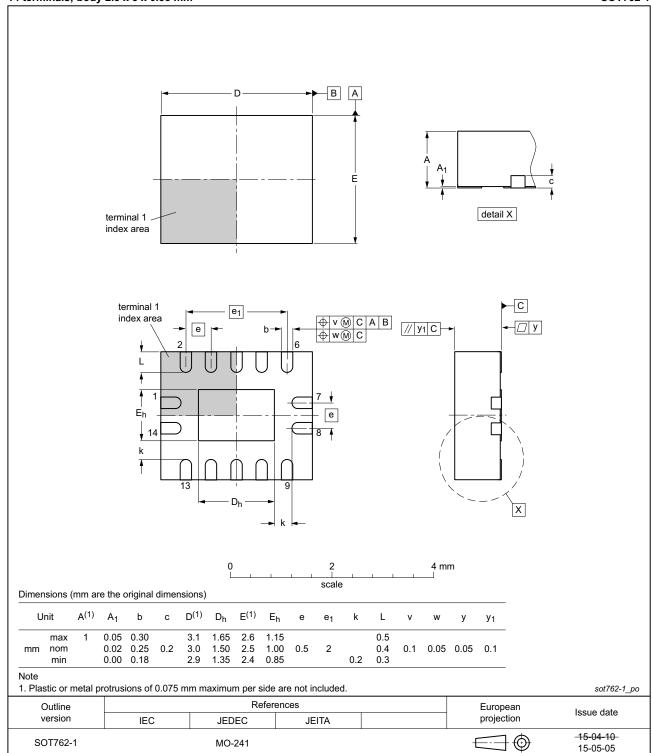


Fig 21. Package outline SOT762-1 (DHVQFN14)

74HC_HCT4066

14. Abbreviations

Table 14. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4066 v.8	20151203	Product data sheet	-	74HC_HCT4066 v.7
Modifications:	Type numbers	s 74HC4066N and 74HCT4066	SN (SOT27-1) remov	ved.
74HC_HCT4066 v.7	20130402	Product data sheet	-	74HC_HCT4066 v.6
Modifications:	Descriptive tit	le corrected (errata).		
	New general	description (errata).		
74HC_HCT4066 v.6	20120718	Product data sheet	-	74HC_HCT4066 v.5
Modifications:		this data sheet has been rede	signed to comply wi	th the new identity
	 Legal texts ha 	ave been adapted to the new c	ompany name wher	e appropriate.
74HC_HCT4066 v.5	20041111	Product data sheet	-	74HC_HCT4066 v.4
74HC_HCT4066 v.4	20030617	Product data sheet	-	74HC_HCT4066_CNV v.3
74HC_HCT4067_CNV v.3	19981110	Product data sheet	-	74HC_HCT4066_CNV v.2
74HC_HCT4066_CNV v.2	19981002	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74HC_HCT4066

74HC4066; 74HCT4066

Quad single-pole single-throw analog switch

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